

Atomic transport at charged graphene: why hydrogen and oxygen are so different

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Using density-functional calculations, we show that electron or hole doped graphene can strongly change the mobility of adsorbed atoms H and O. Interestingly, charge doping affects the diffusion of H and O in the opposite way, namely, electron doping increases/reduces while hole doping reduces/increases the diffusion barrier of H/O, respectively. Specifically, on neutral graphene the diffusion barriers of O and H are 0.74 and 1.01 eV, which are, upon a hole doping of $+5.9 \times 10^{13} \text{ cm}^{-2}$, 0.90 and 0.77 eV, and upon an electron doping of $-5.9 \times 10^{13} \text{ cm}^{-2}$, 0.38 and 1.36 eV, respectively. This means, within the harmonic transition state theory, at room temperature, the diffusion rate of O can be decreased or increased by 470 or 2.2×10^7 times, and that of H can be increased or decreased by 10^5 or 7×10^7 times, by that hole or electron doping level. The difference between the H and O cases is interpreted in terms of the difference in geometric and bonding changes upon charge doping.

Functionalizing graphene by means of adsorbed atoms has various implications such as electronics or catalysis. Interactions between these species and graphene are therefore of much studied topics.^{1,3-6} Fundamentally, besides the stability of the adsorbed atoms or molecules, their dynamics under certain conditions is also a non-trivial facet that needs to fully be taken into account towards realistic applications. There are several factors that largely influence the diffusion of an adsorbate on graphitic support, including contact with solid surfaces,^{7,8} co-adsorption,^{5,9,10} lattice strain,¹¹ and charge doping.^{2,3,14} The latter, possibly controlled by a gate bias in a device, increases/reduces the mobility of O, H or F atoms when electrons/holes are injected.^{3,14}

In this work, based on density-functional calculations, we show that electron/hole doping affects the adsorption of H and O in opposite ways, and analyze origins of this difference. Technically, a graphene unit cell of 4×4 periodicity was adopted, with a vacuum layer of 16 Å separating graphene sheets. We conducted spin-polarized plane-wave density-functional calculations using the PBE functional,¹⁵ and ultrasoft pseudopotentials,¹⁶ as encoded in the Quantum ESPRESSO package.¹⁷ A kinetic cutoff of 40 Ry was applied. The charge analysis method proposed by Bader was adopted.¹⁹ A 3×3 k-point grid was applied to sample the Brillouin zone in self-consistent calculations. A denser k-point grid of 8×8 was used for electronic density of states analyses.²⁰ Electron or hole doping was simulated by adding or removing an amount of electrons, technically, this amount was counterbalanced by a same amount of background charge of opposite sign to avoid the divergence the total energies. Diffusion barriers were determined by the so-called climbing image elastic band methods,¹⁸ with 9 images in each band. A force convergence threshold of 10^{-3} and 10^{-4} a.u. was applied in geometry and band optimizations, respectively. The

binding energy of H or O with graphene here is approximately given by $\Delta E_b = E(*X) - E(X)$ ($X=H,O$), where $E(*X)$ and $E(X)$ is the total energy when X is adsorbed on graphene or placed in a mid point of the vacuum layer, respectively. Here, a doping level of $+5.9 \times 10^{13} \text{ cm}^{-2}$ corresponds to that 0.5 holes are added to the unit cell.

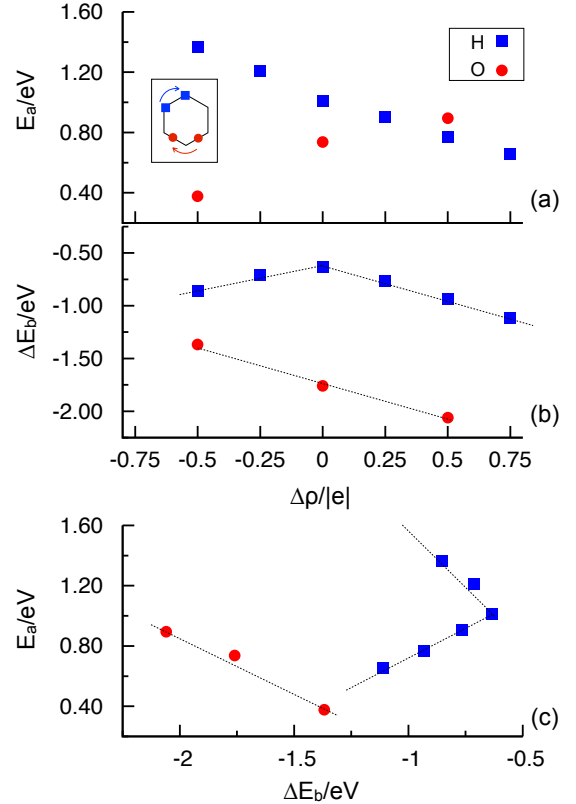


FIG. 1. Diffusion energy barrier E_a (a) and binding energy ΔE_b (b) against the charge doping level. E_a against ΔE_b (c).

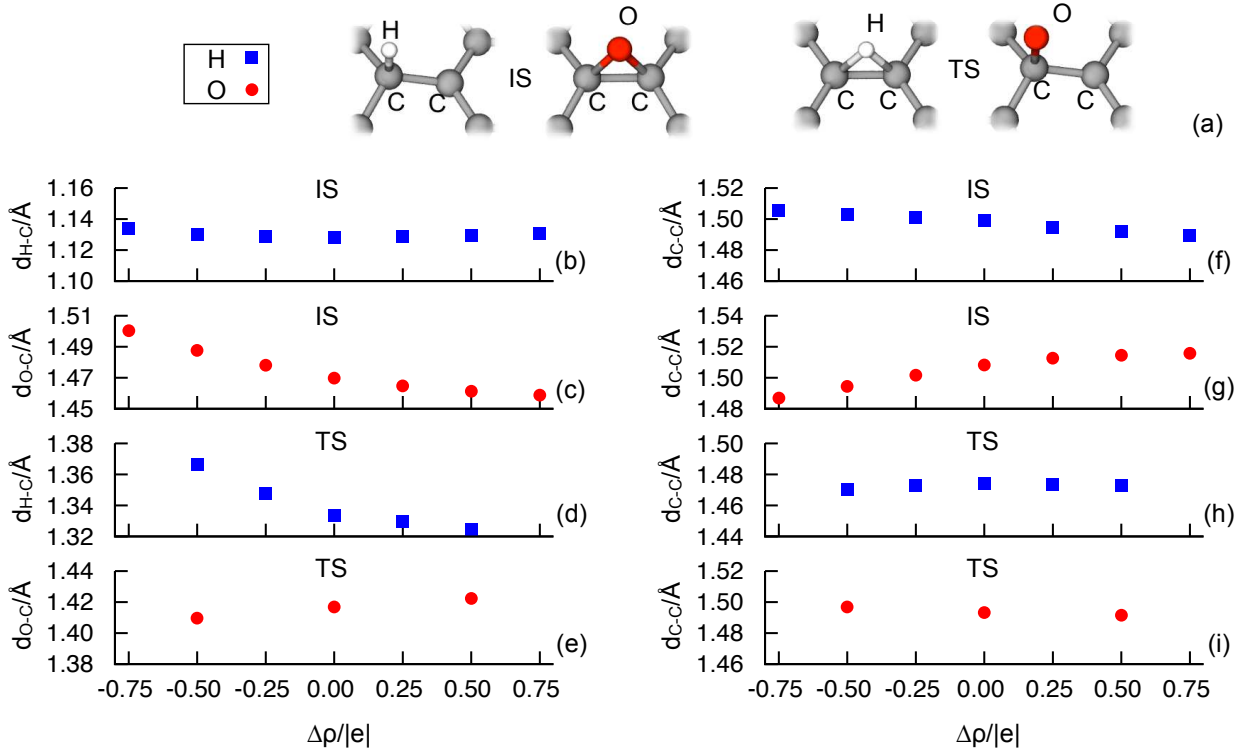


FIG. 2. Properties against the amount of charge added $\Delta\rho$ to the unit cell: (a) Diffusion energy barrier of O and H on graphene, the inset shows the migration of a H/O atom from an ontop/bridge site to a neighboring ontop/bridge site on graphene; (b) and (c) HC and OC bondlengths in the IS, (d) and (e) that in the TS; (g) and (h) the CC bondlength in the IS of H and O diffusion, respectively, (h) and (i) that in the TS.

H, as a monovalent species, is most stabilized at an ontop site (above a C atom) of graphene.^{5,9} O, on the other hand, is found to be more stable at a bridge site (above the middle point of a CC bond).⁷ Upon H or O adsorption, the initial sp^2 hybridization in their bonding partners is transferred to the sp^3 hybridization. The diffusion of H or O in this work is a process in which H or O jumps from one adsorption site to an adjacent equivalent. In Fig 1(a) we show the diffusion energy barriers of H and O on graphene against the charge doping level. In agreement with a previous theoretical work,³ our calculations predict that electron doping lowers, while hole doping increases, the diffusion energy barrier of O. It is also in agreement with various theoretical works^{3,11} that the barrier of in the case of neutral unit cell is estimated at 0.74 eV. The doping of 0.5 electrons leads to a barrier of 0.38 eV and the doping of 0.5 holes leads to a barrier of 0.90 eV. The graph clearly suggests an opposite trend for H diffusion, that is, electron doping increases while hole doping increases the barrier. Similar to previous studies,⁵ without charge doping, the diffusion energy barrier of H is calculated to be 1.01 eV. We determined the diffusion process if H considering five charge doping points, namely, 0.50, 0.25 electrons, and 0.25, 0.50, 0.75 holes added to the unit cell. The diffusion barrier is 1.36, 1.21, 0.90, 0.77, 0.65 eV, respectively. The change in diffusion barrier with respect to the charge doping level

here leads to interesting implications. Within the harmonic transition state theory, the diffusion rate is given by Vineyard's equation $k = \nu_0 e^{-E_a/k_B T}$,¹² the prefactor ν_0 is assumed to be same for all charge doping levels, at room temperature the diffusion rate of H can be decreased or increased by 7×10^7 or 10^5 times, and that of O can be increased or decreased by 2.2×10^7 or 470 times, by adding 0.5 holes or electrons to the unit cell, respectively. Fig1(b) shows the binding energy against the charge doping level. While the binding energy of O is smaller (closer to zero) against electron doping larger against hole doping, the binding energy of H is larger against both electron and hole doping. Fig. 1(c) indicates that O on graphene obeys the Brønsted-Evans-Polanyi principle which suggests a linear relationship between the diffusion barrier of an adsorbed species on a surface and its binding energy,¹³ the stronger the O-graphene bonding is, the higher diffusion barrier would be scaled. For H, this only holds, with electron doping, and becomes violating, with hole doping.

To provide insights into the origin of the difference between the O and H cases, we first examine structural properties of the initial state (IS) and transition state (TS). In the IS, as shown in Fig. 2(b,c), the CH bondlength, which is minimal at zero charge doping, is slightly changed upon charge doping, while the CO bond become considerably elongated/shortened with

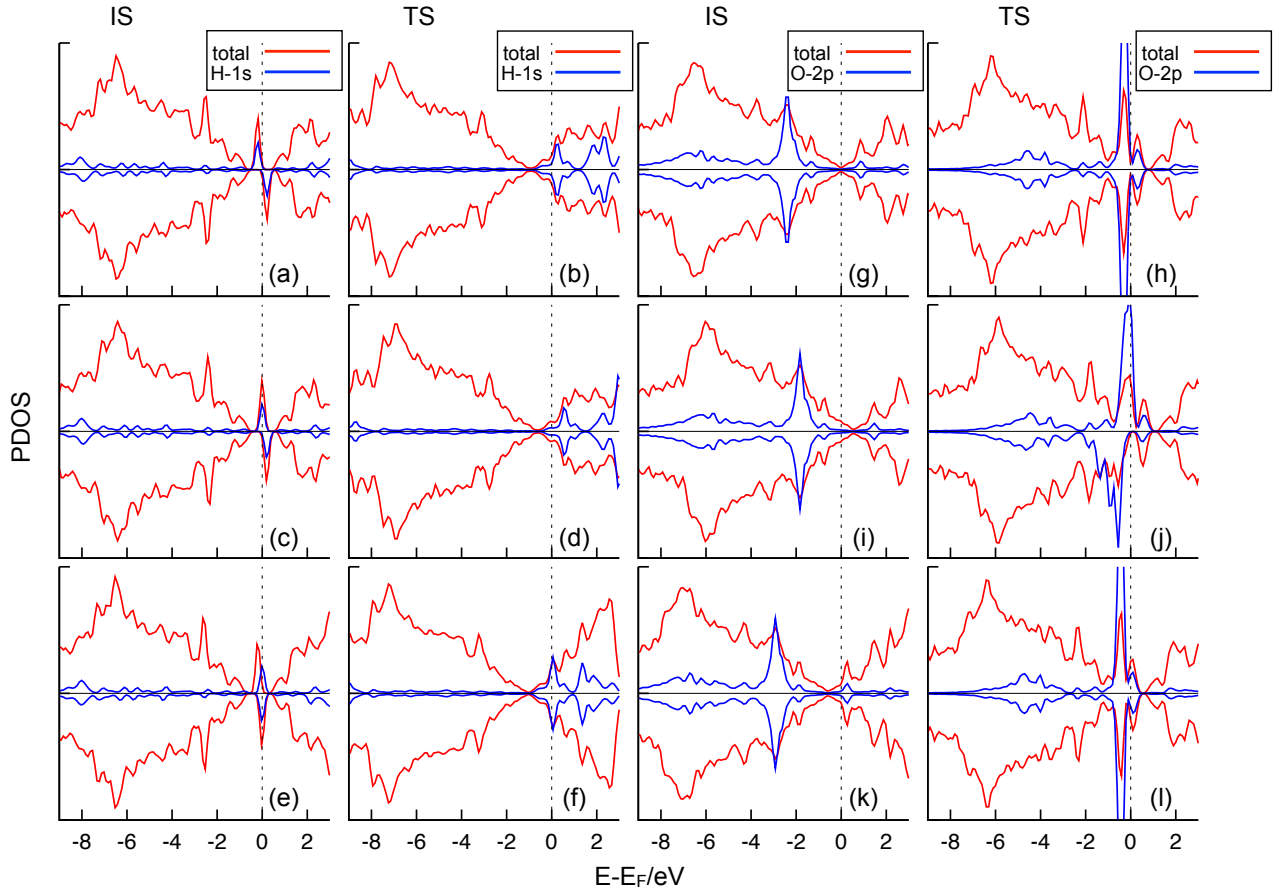


FIG. 3. Density of states : (a,b,g,h) no charge doping, (c,d,j,i) $0.5 |e|$ added to the unit cell, (e,f,k,l) $-0.5 |e|$ added to the unit cell; (a,c,e) IS of H on graphene, (b,d,f) TS of H on graphene, (g,i,k) IS of O on graphene, and (h,j,l) TS of O on graphene. The H-1s PDOS is scaled by 8 times and O-2p PDOS is scaled by 4 times.

electron/hole doping. In particular, in the range of $(-0.75, +0.75) |e|$ doping, the C-H bondlength variation is 0.006 \AA , which is an order small than that of the CO bond, 0.042 \AA . The bondlength changes suggest that the local CH bonding might not really be affected by charge doping while the CO bond is strengthened by hole doping and weakened by electron doping. In the TS, on the other hand, Figs. 2(e,f) indicates that the CO bond is slightly increased, from 1.410 to 1.422 \AA , while the CH bonds are largely decreased from 1.366 to 1.325 \AA , when the doping level changes from -0.5 to $+0.5 |e|$, respectively.

How does the vicinity of H or O in the graphene surface react to charge doping? Fig. 2(f) shows the bondlength of the C bonding partner of H and its C neighboring atoms, and Fig. 2(g) shows that of the two C bonding partners of O, in the IS. In the case of H adsorption, the CC bondlength is decreased from 1.503 \AA ($-0.5 |e|$ doping) to 1.492 \AA ($+0.5 |e|$ doping), in the O adsorption case, on the other hand, the CC bondlength is increased from 1.494 \AA ($-0.5 |e|$ doping) to 1.514 \AA ($+0.5 |e|$ doping). That means, electron doping enhances or reduces, while hole doping reduces or enhances, the CC bonding upon H or O adsorption. In the TS, it seems opposite. Although data plotted in Fig. 2(h and i) implies a little change in

the CC bondlength against the charge doping level, the CC bond is shortened/elongated by hole doping in the case of O diffusion, while it is maximized by zero charge doping in the case of H diffusion.

To this end, in the case of O, there is a clear correlation in the bondlength between the CO and CC bonds, in both the IS and TS, the former is reduced while the latter is increased, and vice versa, upon charge doping. No clear correlation between the CH and CC bonds was found, in both IS and TS, if the CH bondlength varies strongly the CC just slightly changes, and vice versa, upon charge doping. From the geometry considerations, the energy barrier reduction/increase in the case of O upon electron/hole doping is in combination between the weakening/strengthening of CO bond in the IS and its strengthening/weakening in the TS. For H, seemingly, only the weakening/strengthening of the CH bond in the TS caused by electron/hole doping leads to the reduction/increase of the diffusion barrier.

How geometric properties presented above correlated with electronic properties? Fig. 3(a-b) show the projected density of states (DOS) of H on graphene, in the IS and TS structures. As indicated by previous studies,^{1,4,5} the adsorption of a H atom leads to an energy gap^{1,4,5}

caused by H^+ ionic core potential^{1,5} in the energy spectrum of graphene. This is demonstrated with Fig. 3(a). Note that upon H adsorption a $2p_z$ electron of the carbon lattice is unpaired, resulting in unequal numbers of $2p_z$ electrons available in sublattices A and B of graphene, therefore, there exist an occupied spin-up and unoccupied spin-down gap states, Fig. 3(a), and system thus carries a magnetic moment of $1 \mu_B$. From a chemical point of view, this unpaired electron destabilizes the stability of the system due to graphene lattice is constituted since it locally contravenes Hückel's rule. In the TS, Fig. 3 (b), the PDOS shows that a Dirac-like point appears at an energy 0.9 eV lower than the Fermi level. Importantly, no magnetic moment was found in this structure because the H-1s electron interacts with both $2p_z$ electrons of the two C atoms nearby. Note that there are sharp peaks of H-1s PDOS 0.4 eV above the Fermi level, associated with antibonding states between H and the two C atoms. A Bader analysis predicts the H atom in the IS and TS geometries is charged by 0.06 and 0.18 $|e|$, respectively. This implies that the ionic character is increasingly important in bonding of H with the graphene lattice, in the TS. Charge doping leads to similar PDOS, however, it shifts the electronic levels to different energies compared to the Fermi level. In the IS, for example, 0.5 $|e|$ doping changes spin-up gap state from fully occupied to partly occupied (Fig. 3 (c)), while $-0.5 |e|$ doping changes the spin-down gap state from unoccupied to partly unoccupied (Fig. 3 (e)). Consistently, the magnetic moment in the unit cell is now reduced to 0.5 μ_B in both cases. Charge doping in this case is clearly a way to "remove" the unpaired electron from the system, making interatomic bonding in the graphene lattice stronger and then the reactivity of this lattice to H lower, this is a reason why the C-H bond is (slightly) longer upon charge doping. Note, however, that the somewhat longer CH bond upon charge doping does not mean H binds less strongly to the carbon lattice, Fig. 1(b) suggests the opposite. When H and graphene are apart, both hole and electron doping reduces the bond order of C-C bonds weakening the C-C bonding, when H and graphene are bound, both hole and charge doping reduces the unpaired electron effect, enhancing the C-C bonding. A overall result is that charge doping stabilizes H on graphene. The adsorption of H on graphene cannot fully be described by local interactions between H and a C atom since it is a collective process with a delocalized $2p_z$ electron involved.⁴ The PDOS shifted to the higher or lower energies hole or electron doping is also found in the TS, see Fig. 3(d-f). Note that electron doping makes the antibonding states right above the Fermi level occupied, Figs.3(b) and (f), thereby weakening the CH bonds.

To have a clearer picture of where the additional electrons and holes located we calculated the electron or hole addition density by $\Delta\rho_{\text{ele/hole}}(\mathbf{r}) = \rho^{-/+}(\mathbf{r}) - \rho^0(\mathbf{r})$, where $\rho^{-/+}(\mathbf{r})$, $\rho^0(\mathbf{r})$ are the electron density of $-/+0.5 |e|$ and zero charged systems, all calculated in the zero charged geometries. As indicated by Fig. 4(a), in the IS,

the added electrons or holes are mainly associated with the 1s orbital of H and $2p_z$ orbitals of C atoms surrounding the CH bond (we called these C atoms C_3). We found that upon electron or hole doping, there is an electron depletion or accumulation in the sp^2 orbitals of C_3 , that may reduce or enhance the bonding between C_3 and the C atom bound to H, consistent with the decrease or increase in the bondlength shown in Fig. 2 (f). We found a small electron depletion above the C atom in the CH bond upon electron doping this may explain a slightly elongation of this bond, Fig. 2 (b). Note that there is a small electron accumulation above this C atom upon hole doping, but the the CH bond is still slightly elongated, Fig. 2 (b), the reason could be that the C-C bonds in this case is strengthened, moreover, the that weakens the CH bond. In the TS, added electrons or holes are also associated with the H-1s and C_3 - $2p_z$ orbitals. Note that, as mentioned above, the ionic polarization stabilizes the CH bonds in the TS, added electrons/holes will reduce/enhance this polarization, then, weakens/strengths the CH bonds, thereby increasing their length, Fig. 2(d).

Clearly, both occupied and unoccupied states are made mainly up by the $2p_z$ orbitals of the three surrounding C atoms of the C-H bond, and little by H-1s orbital (see also, Fig. 3(a)). This may explain why adding holes or electrons only slightly change the H-C bondlength (see Fig. 2(b)), but much more strongly influences the CC bond (see Fig. 2(f)). Hole doping reduces the repulsion between these C atoms caused by the the interactions between the sp^3 (of C bound to H) and $2p_z$ (of C_3), thereby, reducing the CC bondlength, as indicated in Fig. 2(f).

We now analyze the PDOS in the case of O. In the IS, very different from the DOS of H on graphene, the DOS of O on graphene in the IS shows no bandgap, Fig. 3(g). The hybridization of O- $2p_z$ and C- $2p_z$ results in bonding states lying well below, and antibonding states well above, the Fermi level. Adding electrons or holes shifts electronic energy levels to the left or the right of the Fermi level, Fig. 3(i)(k), making them occupied or empty. This is supported with Fig. 4(c), moreover, upon electron or hole doping, there is a small depletion or accumulation of electron above the two C atoms bound to O. This gives an idea why CO bond is weakened by electron doping and strengthened by hole doping. This also leads to the the strengthening and weakening of the CC bond, upon charge doping, as indicated in Fig. 2(g), also explains the stability of O on graphene against charge doping, Fig. 1(b). For the TS, the PDOS exhibits very sharp peaks right below the Fermi level, which shows more O- $2p_x$, $2p_y$ characters, Figs. 3(h) and 4(d). There is are lower peaks right above the Fermi level, which are associated with O- $2p_z$ orbitals, Figs. 3(h) and 4(d). Hole doping makes the sharp peaks partly unoccupied, Fig. 3(j) that destabilizes the CO bond. Moreover, there is an electron depletion or accumulation in the in the CC bonds upon electron or hole doping. This is an interpretation of why the CO or CC bond is shortened or elongated by electron doping, and vice versa. Finally, from a Bader analysis,

FIG. 4. Added electron (in yellow) and hole (in green) density, isosurface value set at 0.001 au: (a) and (b) H on graphene in the IS and TS; (c) and (d) O on graphene in the IS and TS.

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